

N-channel TrenchMOS logic level FET Rev. 02 — 7 February 2011

Product data sheet

Unit

V

Max

55

Тур

1. **Product profile**

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- 1.3 Applications
 - 12 V and 24 V loads
 - Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data Symbol Parameter Conditions Min T_i ≥ 25 °C; T_i ≤ 175 °C drain-source V_{DS} voltage

I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	43	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	94	W

Suitable for logic level gate drive sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids



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Table 1.	Quick reference da	tacontinued					
Symbol	Parameter	Conditions	N	Min	Тур	Max	Unit
Static cha	racteristics						
R _{DSon} drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-		-	27	mΩ	
	resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-		19	22	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } Figure 12;$ see Figure 13	-		21	25	mΩ
Avalanche	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 43 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ T_{\text{j(init)}} &= 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-		-	123	mJ

	Table '	1. (Quick	reference	data	continued
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Pinning information 2.

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT428 (DPAK)

Ordering information 3.

Table 3. Orderin	g information		
Type number	Package		
	Name	Description	Version
BUK9225-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

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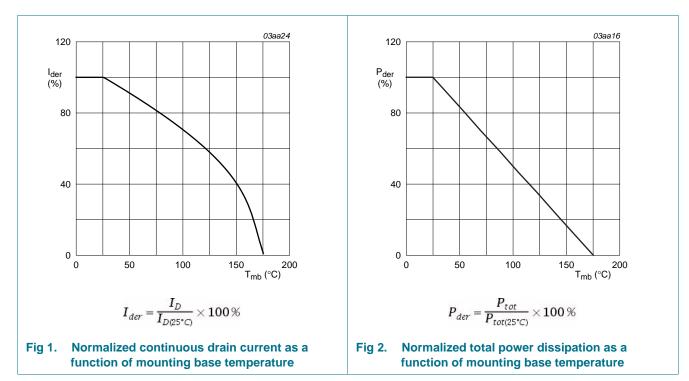
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

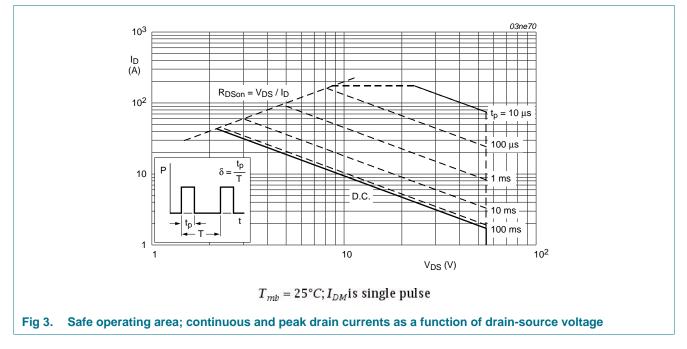
Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
V _{GS}	gate-source voltage			-15	15	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 5 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$		-	43	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>		-	30	А
I _{DM}	peak drain current	$T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}; $ see Figure 3	1	-	173	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	94	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C		-	43	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	173	А
Avalanche r	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 43 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	123	mJ

[1] peak drain current is limited by chip, not package.



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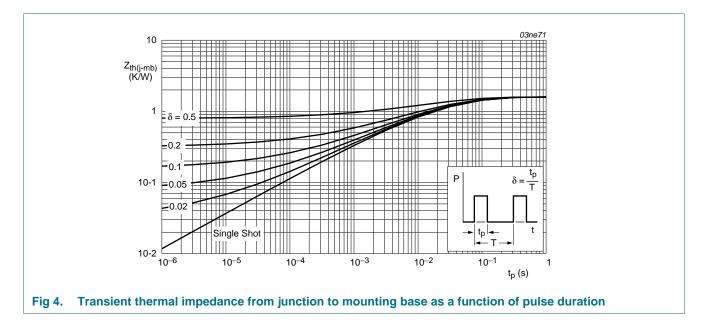
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	-	1.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient		-	71.4	-	K/W

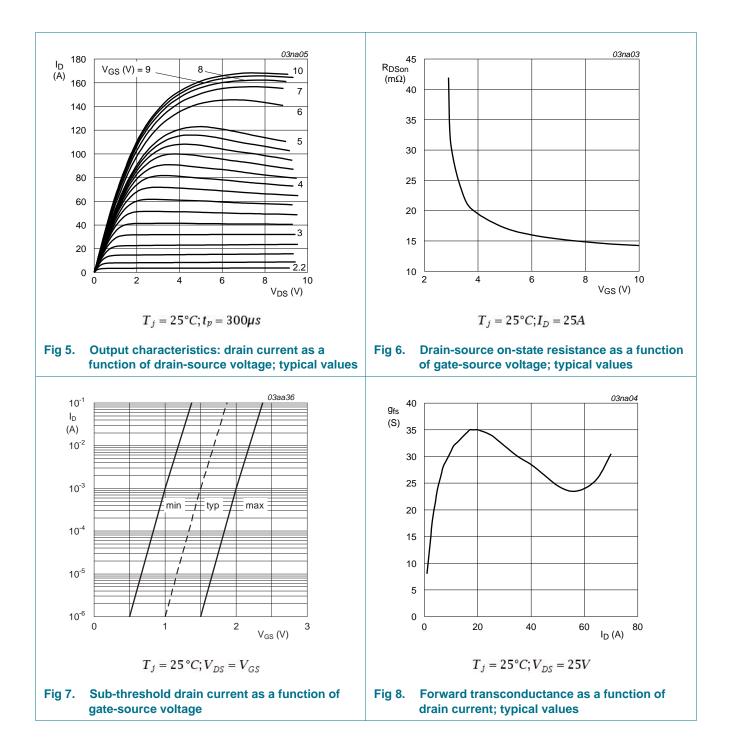


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = -55 °C	50	-	-	V
V _{GS(th)} gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	1	1.5	2	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.3	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; \text{ T}_{j} = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	27	mΩ
resistance	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	50	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	19	22	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	21	25	mΩ
Dynamic	characteristics					
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	1360	1724	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	240	287	pF
C _{rss}	reverse transfer capacitance		-	160	222	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 10 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	104	-	ns
t _{d(off)}	turn-off delay time		-	82	-	ns
t _f	fall time		-	80	-	ns
L _D	internal drain inductance	measured from drain to centre of die ; $T_j = 25 ^\circ\text{C}$	-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	50	-	ns
Qr	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	85	-	nC

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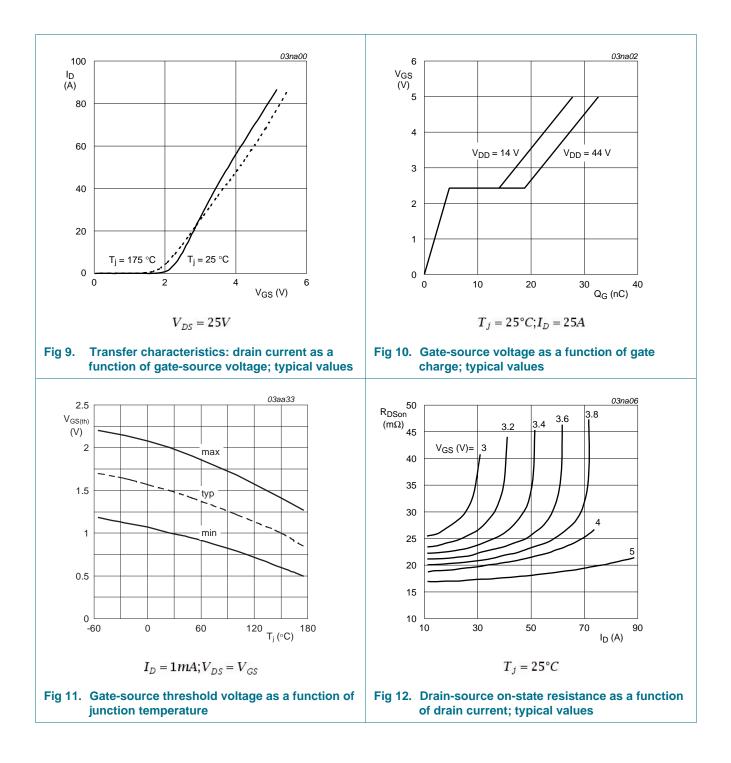
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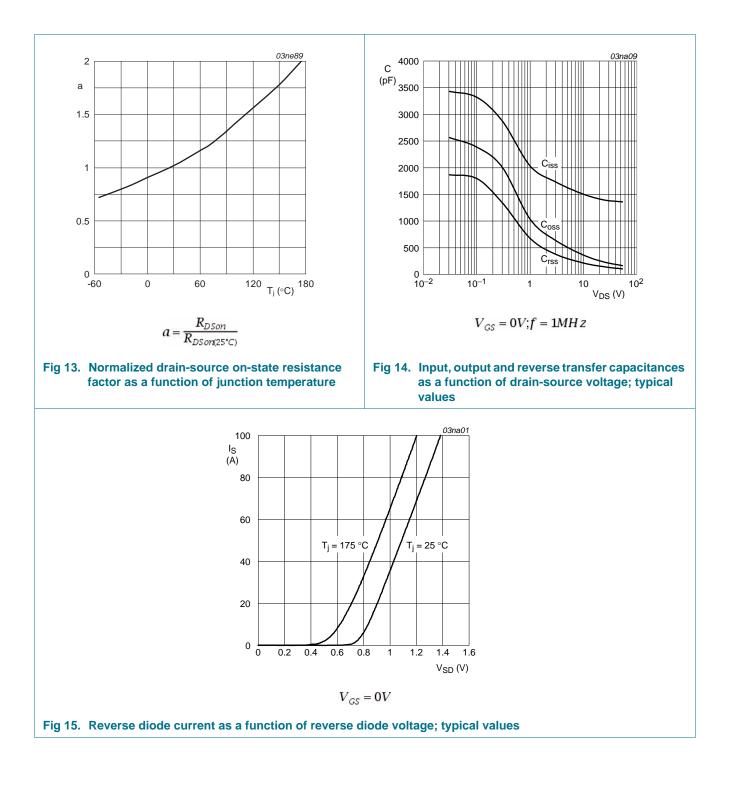
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7. Package outline

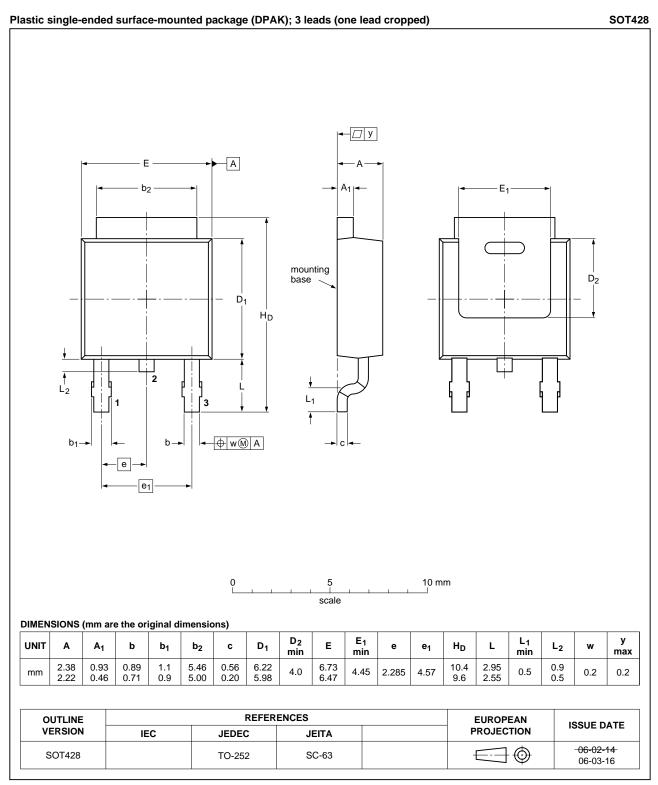


Fig 16. Package outline SOT428 (DPAK)

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BUK9225-55A

8. Revision history

Table 7. Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9225-55A v.2	20110207	Product data sheet	-	BUK9225-55A v.1
Modifications:	of NXP Semic	this data sheet has been reconductors. ave been adapted to the new		
	 Various chang 	ges to content.		
BUK9225-55A v.1	20010417	Product specification	-	-

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9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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